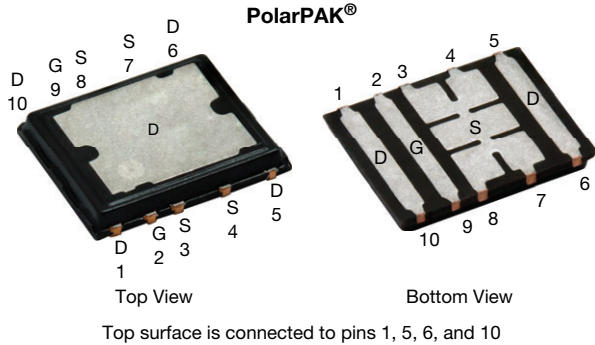


## N-Channel 25 V (D-S) MOSFET



### FEATURES

- TrenchFET® Gen III power MOSFET
- Ultra low thermal resistance using top-exposed PolarPAK® package for double-sided cooling
- Leadframe-based encapsulated package
  - Die not exposed
  - Same layout regardless of die size,  $\leq 100$  V
- Low  $Q_{gd}/Q_{gs}$  ratio helps prevent shoot-through
- 100 %  $R_g$  and UIS tested
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)

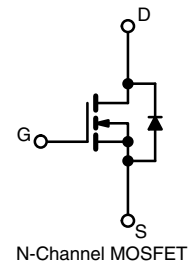


**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

PRODUCT SUMMARY	
$V_{DS}$ (V)	25
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 10$ V	0.0014
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 4.5$ V	0.0018
$Q_g$ typ. (nC)	46
$I_D$ (A) <sup>a</sup> (package limit)	60
$I_D$ (A) <sup>a</sup> (silicon limit)	229
Configuration	Single

### APPLICATIONS

- VRM
- DC/DC conversion: low side
- Server  $V_{CORE}$



ORDERING INFORMATION	
Package	PolarPAK
Lead (Pb)-free and halogen-free	SiE882DF-T1-GE3

ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	$V_{DS}$	25	V
Gate-source voltage	$V_{GS}$	$\pm 20$	
Continuous drain current ( $T_J = 150$ °C)	$I_D$	60 <sup>a</sup> (package limit)	A
		229 (silicon limit)	
		60 <sup>a</sup>	
		47 <sup>b, c</sup>	
Pulsed drain current	$I_{DM}$	100	A
		41 <sup>b, c</sup>	
Continuous source-drain diode current	$I_S$	60 <sup>a</sup>	A
		4.3 <sup>b, c</sup>	
Single pulse avalanche current	$I_{AS}$	50	mJ
Avalanche energy	$E_{AS}$	125	
Maximum power dissipation	$P_D$	125	W
		80	
		5.2 <sup>b, c</sup>	
		3.3 <sup>b, c</sup>	
Operating junction and storage temperature range	$T_J, T_{stg}$	-55 to +150	°C
Soldering recommendations (peak temperature) <sup>d, e</sup>		260	

#### Notes

- Package limited is 60 A
- Surface mounted on 1" x 1" FR4 board
- $t = 10$  s
- See solder profile ([www.vishay.com/doc?73257](http://www.vishay.com/doc?73257)). The PolarPAK is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components



THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient <sup>a, b</sup>	$t \leq 10$ s	$R_{thJA}$	20	24	°C/W
Maximum junction-to-case (drain top)	Steady state	$R_{thJC}$ (drain)	0.8	1	
Maximum junction-to-case (source) <sup>a, c</sup>		$R_{thJC}$ (source)	2.2	2.7	

**Notes**

- a. Surface mounted on 1" x 1" FR4 board  
b. Maximum under steady state conditions is 68 °C/W  
c. Measured at source pin (on the side of the package)

SPECIFICATIONS ( $T_J = 25$ °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-source breakdown voltage	$V_{DS}$	$V_{GS} = 0$ V, $I_D = 250$ $\mu$ A	25	-	-	V
$V_{DS}$ temperature coefficient	$\Delta V_{DS}/T_J$	$I_D = 250$ $\mu$ A	-	25	-	mV/°C
$V_{GS(th)}$ temperature coefficient	$\Delta V_{GS(th)}/T_J$		-	-6	-	
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250$ $\mu$ A	1	1.7	2.2	V
Gate-source leakage	$I_{GSS}$	$V_{DS} = 0$ V, $V_{GS} = \pm 20$ V	-	-	$\pm 100$	nA
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = 25$ V, $V_{GS} = 0$ V	-	-	1	$\mu$ A
		$V_{DS} = 25$ V, $V_{GS} = 0$ V, $T_J = 55$ °C	-	-	10	
On-state drain current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5$ V, $V_{GS} = 10$ V	25	-	-	A
Drain-source on-state resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10$ V, $I_D = 20$ A	-	0.0011	0.0014	$\Omega$
		$V_{GS} = 4.5$ V, $I_D = 20$ A	-	0.0015	0.0018	
Forward transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15$ V, $I_D = 20$ A	-	125	-	S
<b>Dynamic <sup>b</sup></b>						
Input capacitance	$C_{iss}$	$V_{DS} = 12.5$ V, $V_{GS} = 0$ V, $f = 1$ MHz	-	6400	-	pF
Output capacitance	$C_{oss}$		-	1400	-	
Reverse transfer capacitance	$C_{rss}$		-	550	-	
Total gate charge	$Q_g$	$V_{DS} = 12.5$ V, $V_{GS} = 10$ V, $I_D = 20$ A	-	96	145	nC
		$V_{DS} = 12.5$ V, $V_{GS} = 4.5$ V, $I_D = 20$ A	-	46	70	
Gate-source charge	$Q_{gs}$		-	18	-	
Gate-drain charge	$Q_{gd}$		-	12	-	
Gate resistance	$R_g$	$f = 1$ MHz	0.2	1.1	2.2	$\Omega$
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 12.5$ V, $R_L = 1.25$ $\Omega$ , $I_D \cong 10$ A, $V_{GEN} = 4.5$ V, $R_g = 1$ $\Omega$	-	45	70	ns
Rise time	$t_r$		-	170	255	
Turn-off delay time	$t_{d(off)}$		-	65	100	
Fall time	$t_f$		-	85	130	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 12.5$ V, $R_L = 1.25$ $\Omega$ , $I_D \cong 10$ A, $V_{GEN} = 10$ V, $R_g = 1$ $\Omega$	-	20	30	
Rise time	$t_r$		-	15	25	
Turn-off delay time	$t_{d(off)}$		-	45	70	
Fall time	$t_f$		-	10	15	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous source-drain diode current	$I_S$	$T_C = 25$ °C	-	-	60	A
Pulse diode forward current <sup>a</sup>	$I_{SM}$		-	-	100	
Body diode voltage	$V_{SD}$	$I_S = 10$ A	-	0.8	1.2	V
Body diode reverse recovery time	$t_{rr}$	$I_F = 10$ A, $di/dt = 100$ A/ $\mu$ s, $T_J = 25$ °C	-	55	85	ns
Body diode reverse recovery charge	$Q_{rr}$		-	70	105	nC
Reverse recovery fall time	$t_a$		-	25	-	ns
Reverse recovery rise time	$t_b$		-	30	-	

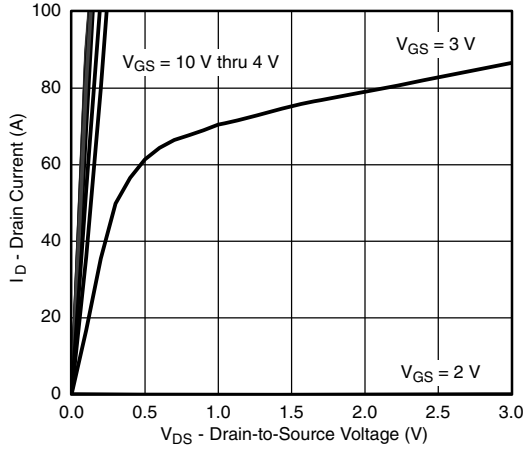
**Notes**

- a. Pulse test; pulse width  $\leq 300$   $\mu$ s, duty cycle  $\leq 2$  %  
b. Guaranteed by design, not subject to production testing

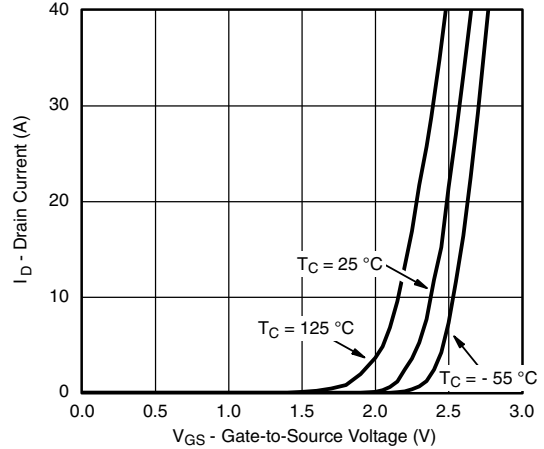
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



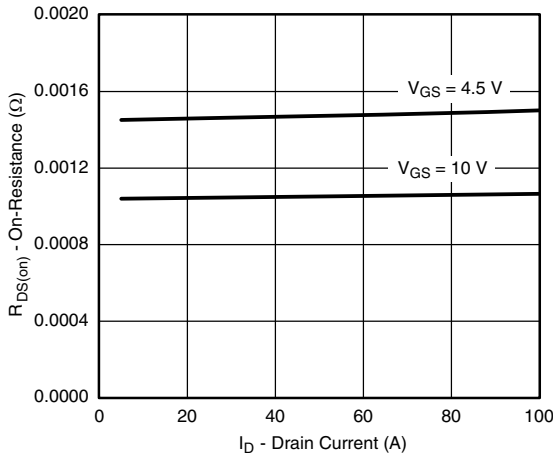
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



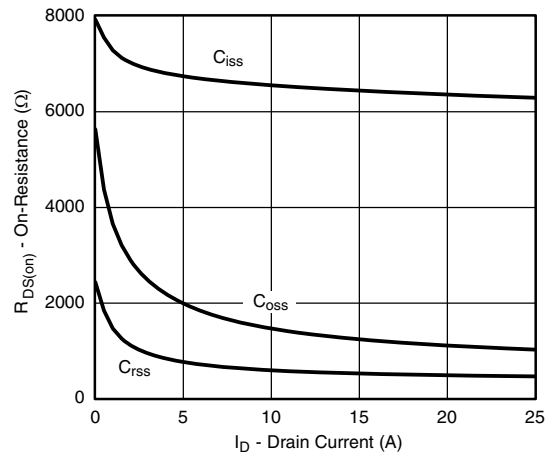
Output Characteristics



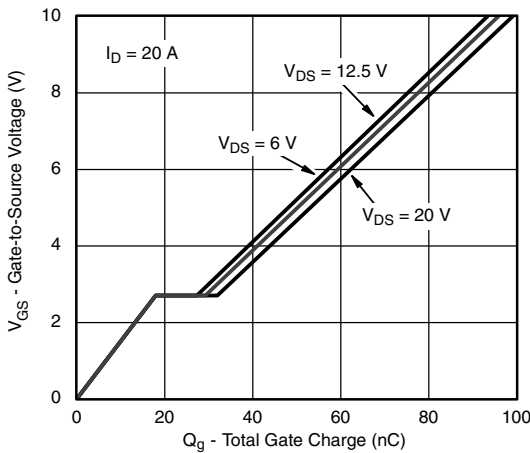
Transfer Characteristics



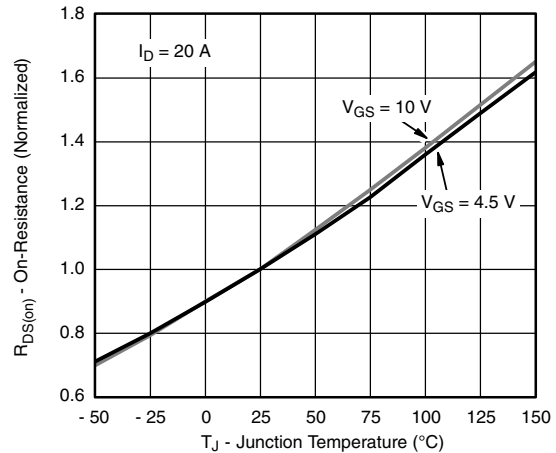
On-Resistance vs. Drain Current and Gate Voltage



Capacitance



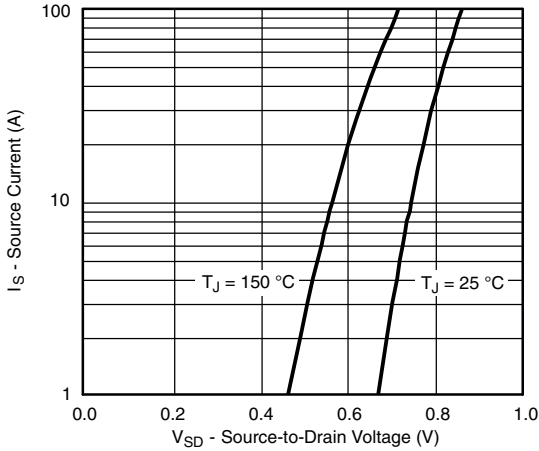
Gate Charge



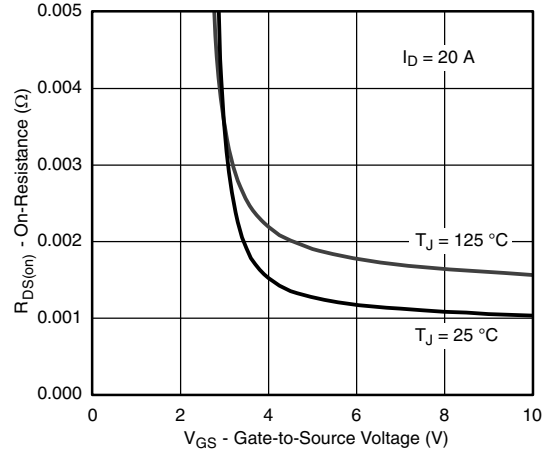
On-Resistance vs. Junction Temperature



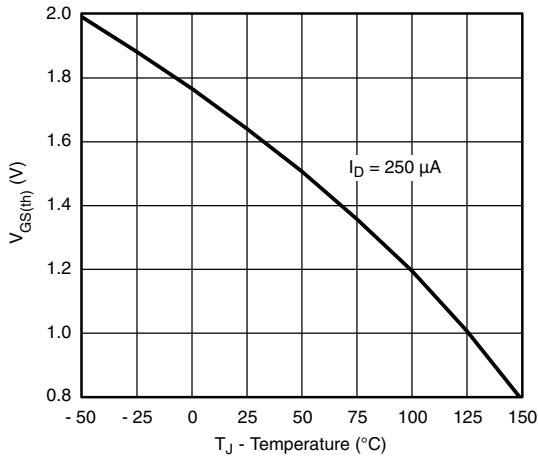
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



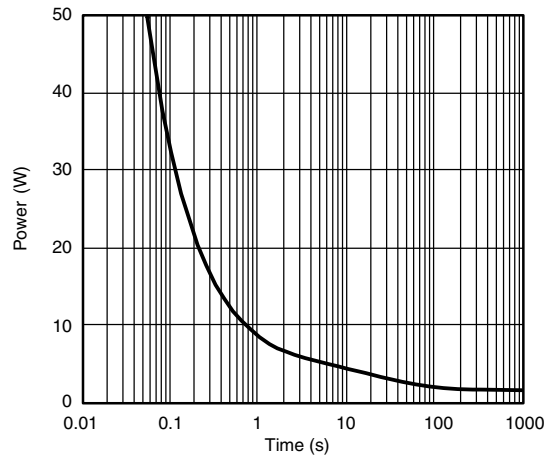
Source-Drain Diode Forward Voltage



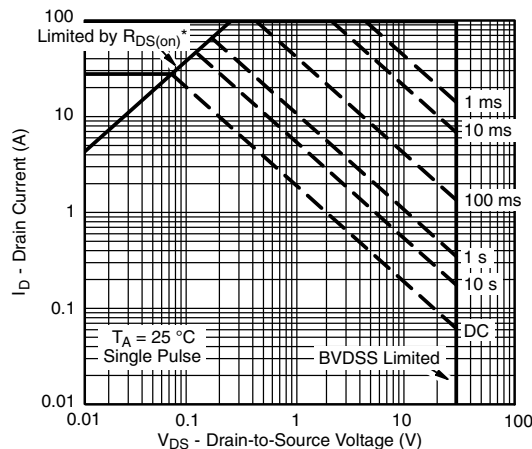
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



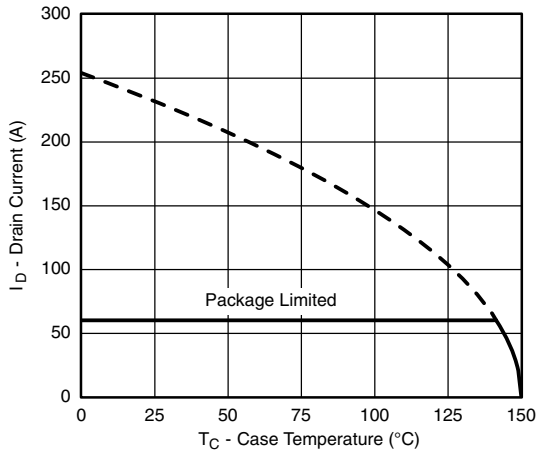
Single Pulse Power, Junction-to-Ambient



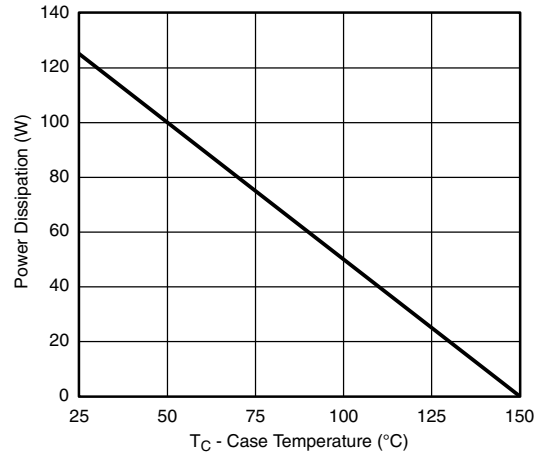
Safe Operating Area, Junction-to-Ambient



**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



**Current Derating <sup>a</sup>**



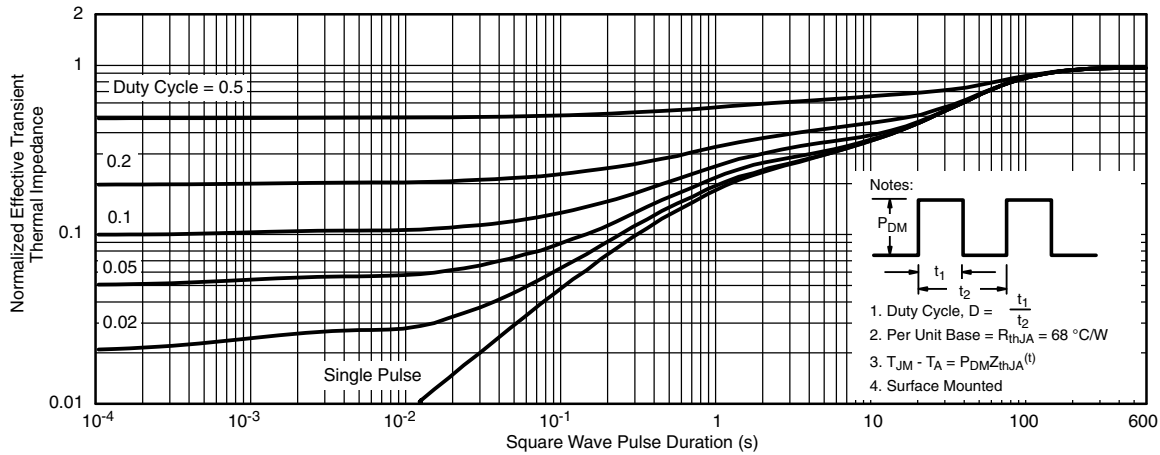
**Power Derating, Junction-to-Case <sup>a</sup>**

**Note**

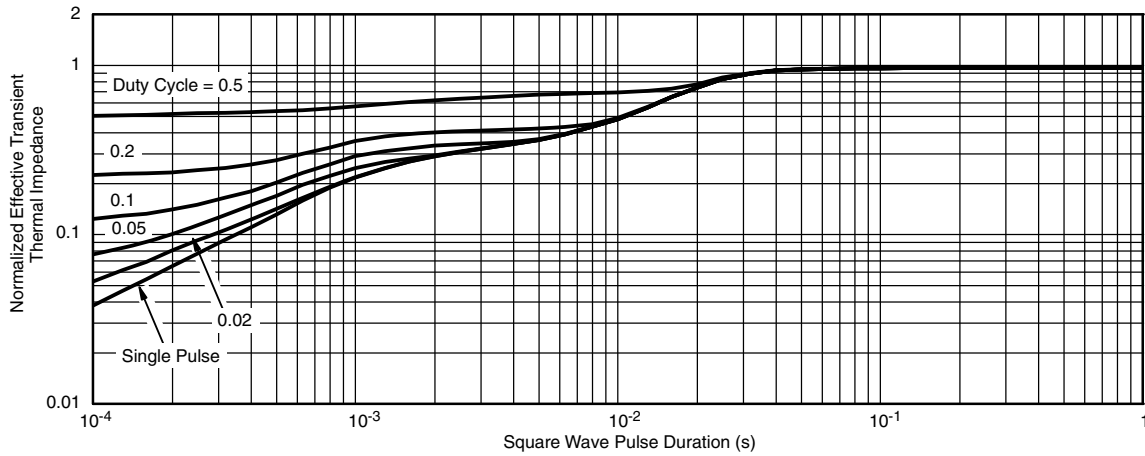
- a. The power dissipation  $P_D$  is based on  $T_J$  max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



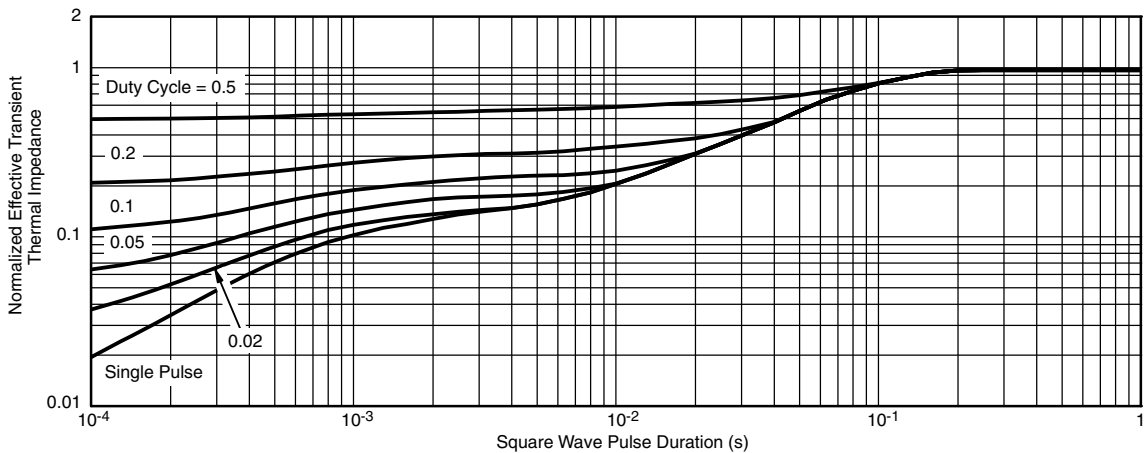
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case (Drain Top)



Normalized Thermal Transient Impedance, Junction-to-Source

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see [www.vishay.com/ppg?65002](http://www.vishay.com/ppg?65002).

## POLARPAK™ OPTION L



(Top View)



DETAIL Z



Product datasheet/information page contain links to applicable package drawing.



View A



View A  
(Bottom View)

# Package Information

Vishay Siliconix



DIM	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.75	0.80	0.85	0.030	0.031	0.033
A1	0.00	-	0.05	0.000	-	0.002
b1	0.48	0.58	0.68	0.019	0.023	0.027
b2	0.41	0.51	0.61	0.016	0.020	0.024
b3	2.19	2.29	2.39	0.086	0.090	0.094
b4	0.89	1.04	1.19	0.035	0.041	0.047
b5	0.23	0.33	0.43	0.009	0.013	0.017
c	0.20	0.25	0.30	0.008	0.010	0.012
D	6.00	6.15	6.30	0.236	0.242	0.248
D1	5.74	5.89	6.04	0.226	0.232	0.238
E	5.01	5.16	5.31	0.197	0.203	0.209
E1	4.75	4.90	5.05	0.187	0.193	0.199
H1	0.23	-	-	0.009	-	-
H2	0.45	-	0.56	0.018	-	0.022
H3	0.31	0.41	0.51	0.012	0.016	0.020
H4	0.45	-	0.56	0.018	-	0.022
K1	4.22	4.37	4.52	0.166	0.172	0.178
K2	1.08	1.13	1.18	0.043	0.044	0.046
K3	1.37	-	-	0.054	-	-
K4	0.24	-	-	0.009	-	-
M1	4.30	4.50	4.70	0.169	0.177	0.185
M2	3.43	3.58	3.73	0.135	0.141	0.147
M3	0.22	-	-	0.009	-	-
M4	0.05	-	-	0.002	-	-
P1	0.15	0.20	0.25	0.006	0.008	0.010
T1	3.48	3.64	4.10	0.137	0.143	0.161
T2	0.56	0.76	0.95	0.022	0.030	0.037
T3	1.20	-	-	0.047	-	-
T4	3.90	-	-	0.153	-	-
T5	0	0.18	0.36	0.000	0.007	0.014
θ	0°	10°	12°	0°	10°	12°

ECN: T-08441-Rev. C, 11-Aug-08  
DWG: 5946

## Notes

Millimeters govern over inches.



## RECOMMENDED MINIMUM PADS FOR PolarPAK® Option L and S



Recommended Minimum for PolarPAK Option L and S  
 Dimensions in mm/(Inches)  
 No External Traces within Broken Lines  
 Dot indicates Gate Pin (Part Marking)



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